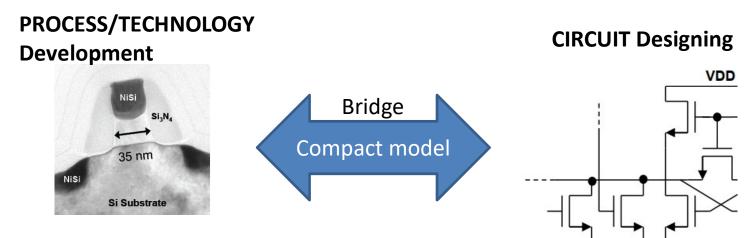
COMPACT MODELING USING VERILOG-A AND INTEGRATION WITH HSPICE

What is a compact model?

-> Computationally efficient description of the terminal properties of a device as a function of terminal voltages





- -> The compact model is implemented inside a circuit simulation engine.
- -> How to make a compact model?

Different types of Compact models:

Physics based

All parameters have physical significance.

Computationally efficient and technology independent.

Empirical

Set of equations with fitting parameters.

Lookup table based

Limited to characterized data present in lookup table.

Macromodels

Present in the form of equivalent circuit representation.

Semi-empirical model

Introduced fitting parameters in Physics based model to capture device behaviour.

Empirical lookup table based model.

Compact model Requirements:

Model stability and convergence

Functions and their derivatives must be continuous

No evaluation resulting 0/0 (i.e. physical limit must be accurately set)

Speed of evaluation

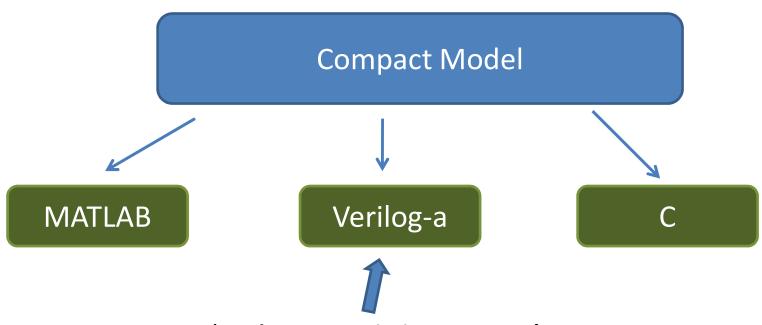
Expensive math functions must be avoided.

Reusability of internal variables to reduce computation time.

Accuracy

Must be accurate up to required RMS error.

Ref: Tutorial on "Basics of Compact Model Development", by Sivakumar P Mudanai (*Intel Corporation, Santa Clara, CA*). Web: https://nanohub.org/resources/21367/



'Hardware Description Language'
Can be easily integrated with SPICE-Simulators

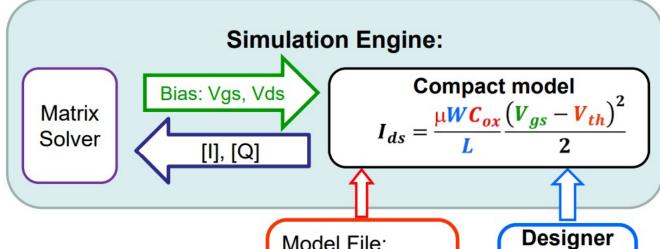
https://nanohub.org/resources/20580/download/2014.0 2.21-Coram-NEEDS.pdf

Circuit Simulators??

- ☐ NgSpice
- ☐ HSpice
- ☐ PSpice
- ☐ MultiSim
- ☐ CadenceSpectre

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SIMPLIFIED VIEW OF A CIRCUIT SIMULATION



Simulation engine iteratively solves for Kirchoffs voltage and current laws.

Model File: **Tox = 20A;...** Vth = 300mV μ = 100cm²/Vs

Design variables

Input:

W=1 μm

L=100nm

Technology details

Verilog-A Model for a Simple Resistor

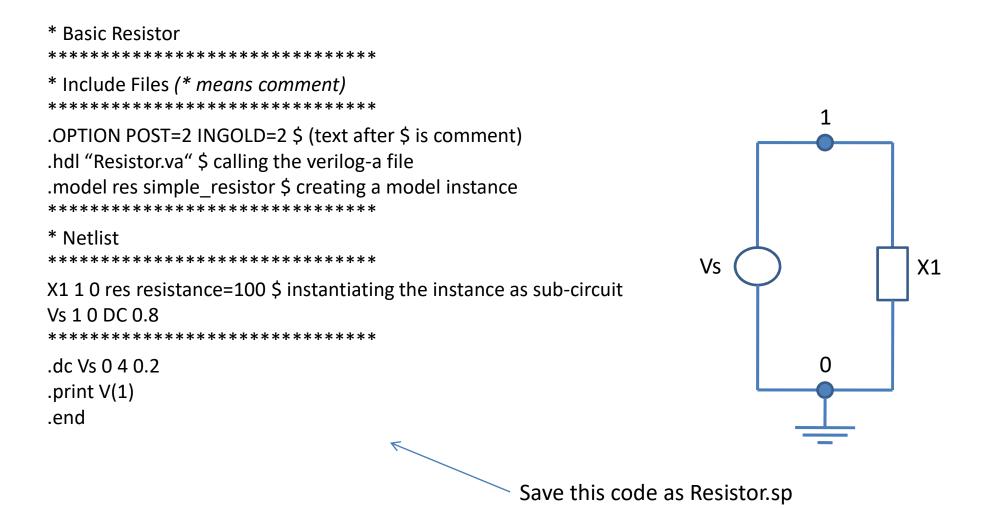
Save the following code as Resistor.va (can use any text editor)

```
include "disciplines.vams"
module simple_resistor(p,n);
inout p,n;
parameter real resistance = 1000.0 from (0.0:inf);
electrical p, n;
analog
begin
I(p,n) <+ V(p,n)/resistance;
end
endmodule</pre>
```

First line includes header files which define "electrical" discipline and access functions V and I (also thermal, kinematic, ...)

https://nanohub.org/resources/20580/download/2014.02.21-Coram-NEEDS.pdf

Hspice file for a Simple Resistor



https://cseweb.ucsd.edu/classes/wi10/cse241a/assign/hspice_sa.pdf

Verilog-A model of a Capacitor

Save the following code as Capacitor.va

```
`include "disciplines.vams"
module simple_capacitor(p,n);
inout p,n;
electrical p,n;
parameter real C=1e-6 from [0.0:inf); //default value
real q;
analog begin
q=C*V(p,n);
I(p,n)<+ ddt(q);
end
endmodule</pre>
```

Q1. Use your customized models for resistor and capacitor to design RC-Low Pass Filter with 3-dB Bandwidth of 1KHz. Perform AC analysis to verify the result. Overwrite appropriate values in place of default values for Resistor and Capacitor. Draw the circuit showing Vs, X1, X2, and node labels.

```
*RC-Check
********Include Files*****
.OPTION POST=2
.hdl "Resistor.va"
.hdl "Capacitor.va"
.model cap simple_capacitor
.model res simple_resistor
****** Netlist *******
X1 1 2 res resistance=What value?
X2 2 0 cap C=What value?
Vs 1 0 AC 1V
********
                                                    Save this code as RC.sp
.AC DEC 10 1 1MEG
.print V(2)
.end
```

Q2(a). Make a Verilog-A model for a simple n-channel MOSFET (NMOS) by defining current equations in linear and saturation regions. Verify by plotting INPUT and OUTPUT characteristics in HSPICE. Consider Vth=0.6V.

```
`include "disciplines.vams"
'include "constants.vams"
                                                                                                    d
module simple NMOS(d,g,s,b);
inout d,g,s,b; // inout TERMINALS
electrical d ,g ,s ,b ; //input-output nodes
parameter real W=1e-5 from [0:inf]; // width of MOSFET
parameter real L=1e-5 from [0:inf]; // Length of MOSFET
parameter real Vth=0.6 from [0:inf]; // Threshold voltage
parameter real mu=1400 from [0:inf];
parameter real NA=1e17 from [1e13:1e22]; // Doping
parameter real TOX=20e-7; // Oxide Thickness
parameter real VSB=0.0; //Body-Bias
real P EPSOX=3.9*8.85e-14;
real P EPSSI=11.7*8.85e-14;
real PHI,GAMMA,COX,PHI F,VT; // You can choose your own variables
                                                                                                   NMOS
real Ni=1e10:
real q=1.6e-19;
analog
begin
// ...... Real variables calculations using the provided equations.......
                                                                                        Save this code as NMOS.va
if (V(g,s) > Vth) //ensuring conduction after threshold
begin
if(.....)
else
end
end
```

endmodule

Reference Hspice code for NMOS

```
* Basic mos test
****** Include Files
.OPTION POST=2 INGOLD=2
.hdl "MOSFET.va" $ change the names according to your file_names
.model mos simple mos $ change module name accordingly
****NETLIST
X1 3 2 0 0 mos
Vdum 4 3 DC 0
$R 4 3 100K $ Uncomment for INVERTER problem
Vdd 4 0 DC 2
Vgg 2 0 DC 2
$ Vgg 2 0 PULSE(0 2.5 5n 2.5n 2.5n 20n 45n) $ uncomment for INVERTER problem
*****Analysis $ LV HV td tr tf PW PER
.dc Vdd 0 2 0.02 $ to plot Output Characteristics
.dc Vgg 0 2 0.02 $ to plot Input Characteristics
                                                             Save this code as NMOS.sp
* .tran 250p 145n $ uncomment for INVERTER problem
$ .print – to get data in the .lis file
.end
```

Q2(b). Design a basic INVERTER using the NMOS and verify by applying a square pulse at Gate.

Q3. Repeat Q2(a) for a PMOS transistor. Plot magnitude of current versus Vds (Vdd=0 to -2V) at Vgg=-2V, and magnitude of current versus Vgs (Vgg=0 to -2V) at Vdd=-2V. Consider Vth=-0.6V.

Note the following differences compared to NMOS: PMOS is ON when Vgs < Vth, is in linear region when Vds >= (Vgs-Vth), and is in saturation when Vds < (Vgs-Vth).

Q4. Design a CMOS inverter using NMOS (from Q2) and PMOS (from Q3) and verify by applying the same input square pulse as in Q2(b), however the pulse oscillates between 0V and 2V in this case. The circuit for CMOS is shown in Fig. A.

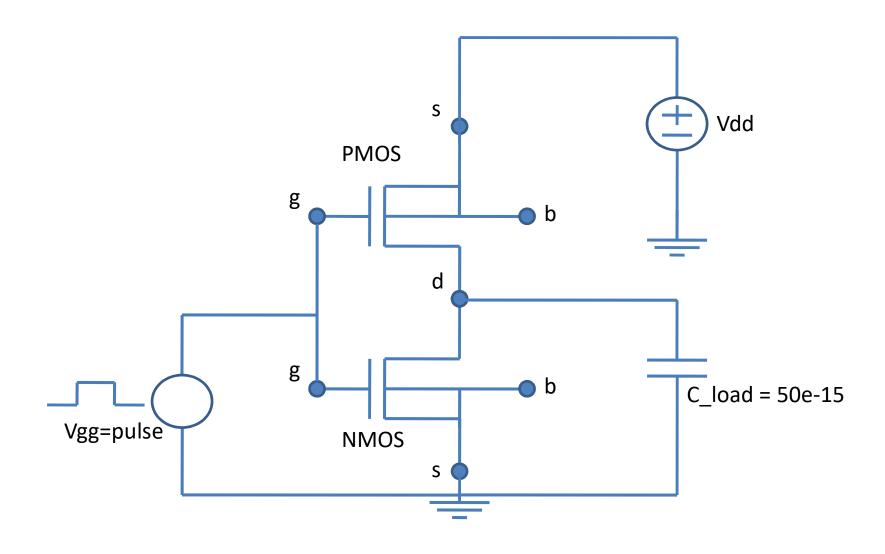


Fig. A: CMOS Inverter circuit